

09/688,203

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1401	438/257	USPAT; EPO; JPO	2002/01/07 18:00
2	BRS	L2	21321	semiconductor adj memory adj device	USPAT; EPO; JPO	2002/01/07 18:01
3	BRS	L3	4902	cell adj transistors	USPAT; EPO; JPO	2002/01/07 18:01
4	BRS	L4	14515	floating adj gate	USPAT; EPO; JPO	2002/01/07 18:01
5	BRS	L5	23925	control adj gate	USPAT; EPO; JPO	2002/01/07 18:02
6	BRS	L6	14750	gate adj insulating adj film	USPAT; EPO; JPO	2002/01/07 18:02
7	BRS	L7	186	electrically adj writing	USPAT; EPO; JPO	2002/01/07 18:02
8	BRS	L8	268	electrically adj erasing	USPAT; EPO; JPO	2002/01/07 18:05
9	BRS	L9	2265	high adj withstand adj voltage	USPAT; EPO; JPO	2002/01/07 18:07
10	BRS	L10	53	1 and 2 and 3	USPAT; EPO; JPO	2002/01/07 18:07
11	BRS	L11	1160	4 and 5 and 6	USPAT; EPO; JPO	2002/01/07 18:08
12	BRS	L12	33	7 and 8	USPAT; EPO; JPO	2002/01/07 18:08

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	35	4 and 5 and 6 and 9	USPAT; EPO; JPO	2002/01/07 18:08

L10

* 6,335,244

- 6,323,085

- 6,235,583

- 6,232,182

- 6,228,714

- 6,214,665

* 6,136,648

- 6,130,110

- 6,030,869

- 6,010,946

* 5,930,629

* 5,863,822

- 5,786,997

- 5,372,963

L12

* 5,683,923

- 5,360,756

- 5,348,898

- 5,252,505

- 5,114,870

- 4,803,529

L13